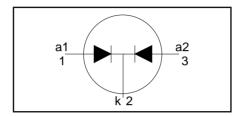
# BYV133, BYV133B series

#### **FEATURES**

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

#### **SYMBOL**



#### QUICK REFERENCE DATA

$$V_R = 35 \text{ V}/ 40 \text{ V}/ 45 \text{ V}$$
 $I_{O(AV)} = 20 \text{ A}$ 
 $V_F \le 0.6 \text{ V}$ 

#### **GENERAL DESCRIPTION**

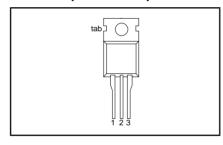
Dual, common cathode schottky rectifier diodes in a conventional leaded plastic package and a surface mounting plastic package. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The BYV133 series is supplied in the SOT78 conventional leaded package. The BYV133B series is supplied in the SOT404 surface mounting package.

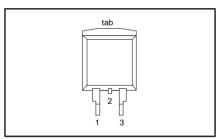
### **PINNING**

PIN	DESCRIPTION		
1	anode 1 (a)		
2	cathode (k) 1		
3	anode 2 (a)		
tab	cathode (k)		

# SOT78 (TO220AB)



#### **SOT404**



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
		BYV133- BYV133B-		35 35	40 40	45 45	
$V_{RRM}$	Peak repetitive reverse voltage		-	35	40	45	V
$V_{RWM}$	Working peak reverse voltage		-	35	40	45	V
$V_R$	Continuous reverse voltage	T <sub>mb</sub> ≤ 120 °C	-	35	40	45	V
I <sub>O(AV)</sub>	Average rectified forward current (both diodes conducting)	square wave; $\delta$ = 0.5; $T_{mb} \le$ 120 °C	-		20		А
I <sub>FRM</sub>	Repetitive peak forward current (per diode)	square wave; $\delta = 0.5$ ; $T_{mb} \le 120 ^{\circ}\text{C}$	-		20		А
I <sub>FSM</sub>	Non-repetitive peak forward current per diode	t = 10 ms t = 8.3 ms sinusoidal; $T_i$ = 125 °C prior to surge; with reapplied $V_{RRM(max)}$	-		100 110		A A
I <sub>RRM</sub>	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T <sub>i max</sub>	-		1		A
T <sub>j</sub>	Operating junction temperature		-		150		°C
$T_{stg}$	Storage temperature		- 65		175		°C

<sup>1.</sup> It is not possible to make connection to pin 2 of the SOT404 pckage.

BYV133, BYV133B series

# THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th i-a</sub>	to mounting base	per diode both diodes SOT78 package in free air SOT404 package, pcb mounted, minimum footprint, FR4 board	1 1 1 1	- 60 50	2.6 1.6 -	K/W K/W K/W K/W

# **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>F</sub>	Forward voltage per diode	$I_F = 7 \text{ A}; T_j = 125^{\circ}\text{C}$ $I_E = 20 \text{ A}$		0.5 0.84	0.6 0.94	\ \ \
I <sub>R</sub>	Reverse current per diode	$\dot{V}_{R} = V_{RWM}$	-	0.1 10	0.8	mA mA
C <sub>d</sub>	Junction capacitance per diode	$V_R = V_{RWM}^{\text{NM}}$ ; $T_j = 100^{\circ}\text{C}$ $V_R = 5 \text{ V}$ ; $f = 1 \text{ MHz}$ , $T_j = 25^{\circ}\text{C}$ to 125°C	- -	210	-	pF

# BYV133, BYV133B series

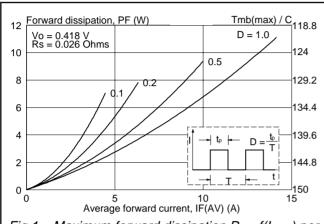


Fig.1. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; square current waveform where  $I_{F(AV)} = I_{F(RMS)} \ x \ \sqrt{D}$ .

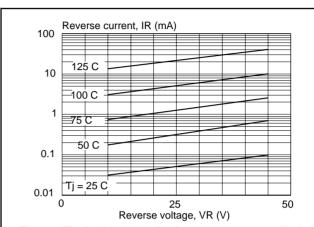


Fig.4. Typical reverse leakage current per diode;  $I_R = f(V_R)$ ; parameter  $T_j$ 

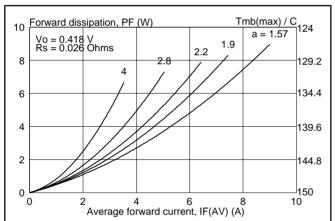


Fig.2. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; sinusoidal current waveform where a = form factor  $= I_{F(RMS)} / I_{F(AV)}$ .

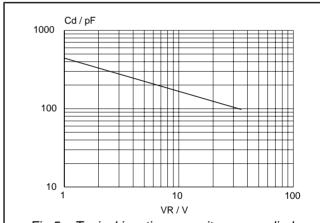


Fig.5. Typical junction capacitance per diode;  $C_d = f(V_R)$ ; f = 1 MHz;  $T_j = 25$ °C to 125 °C.

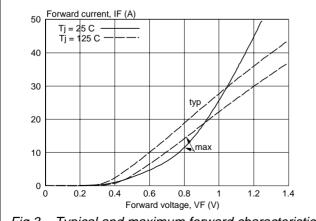


Fig.3. Typical and maximum forward characteristic  $I_F = f(V_F)$ ; parameter  $T_i$ 

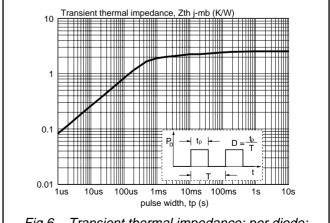
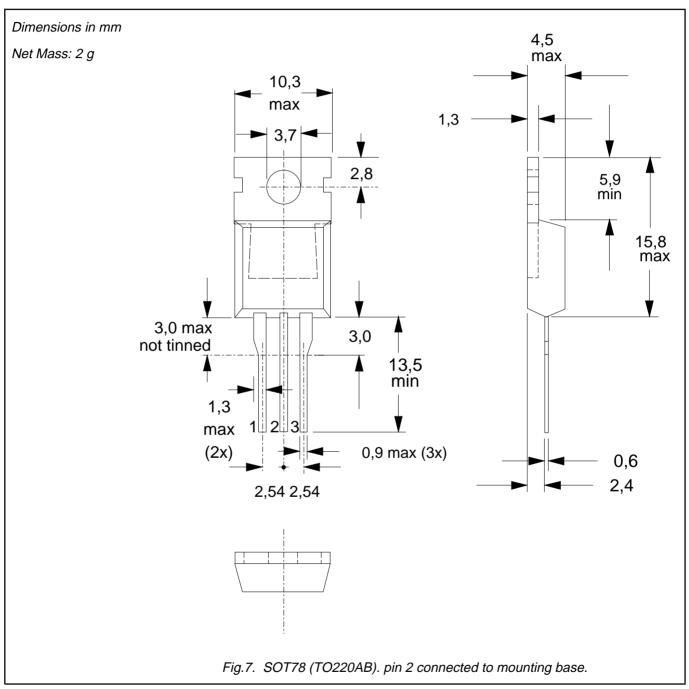


Fig.6. Transient thermal impedance; per diode;  $Z_{th j-mb} = f(t_p)$ .

BYV133, BYV133B series

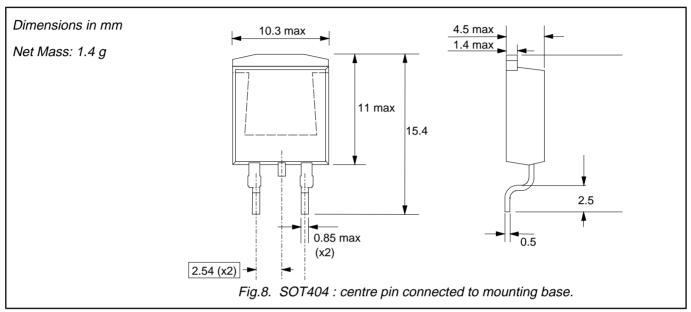
## **MECHANICAL DATA**



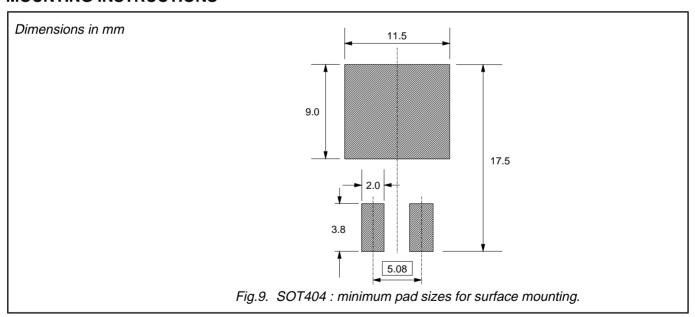
- Notes
  1. Refer to mounting instructions for SOT78 (TO220) envelopes.
  2. Epoxy meets UL94 V0 at 1/8".

BYV133, BYV133B series

# **MECHANICAL DATA**



## **MOUNTING INSTRUCTIONS**



## **Notes**

1. Plastic meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

# Rectifier diodes Schottky barrier

BYV133, BYV133B series

#### **DEFINITIONS**

Data sheet status						
Objective specification This data sheet contains target or goal specifications for product development.						
Preliminary specification This data sheet contains preliminary data; supplementary data may be published la						
Product specification This data sheet contains final product specifications.						
Limiting values						

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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